



Redefining
precision laser optics.

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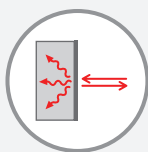
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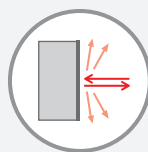
Ultralow-loss and ultrastable coatings **10× lower Brownian noise**



Center wavelength
900 – 2000 nm



Optical absorption
< 1 ppm



Optical scatter
< 5 ppm



Radius of curvature
> 10 cm

Other specifications

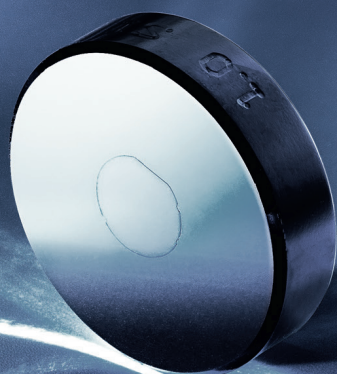
Optical transmission	Tunable, per customer request
Reflectivity	Typically > 99.99 %, with > 99.999 % achievable
Loss angle	$< 4 \times 10^{-5}$ at 300 K, $< 5 \times 10^{-6}$ at 10 K
Coating material	Single-crystal GaAs/AlGaAs
Substrate material	Typically fused silica, other materials available
Temperature range	Cryogenic, room temperature, and high temperature solutions available
Substrate diameter	0.5 - 1 inch (12.7 - 25.4 mm), other sizes available
Surface quality	1 Å RMS micro-roughness
Durability	Similar to fused silica, cleaning instructions provided on request

Select scientific publications

G. D. Cole, et. al. "High-performance near- and mid-infrared crystalline coatings," *Optica*, **3**, 647-656, 2016.

K. U. Schreiber, et. al. "Sensing Earth rotation with a helium-neon ring laser operating at 1.15 μm ," *Optics Letters*, **40**, 1705-1708, 2015.

G. D. Cole, et. al. "Tenfold reduction of Brownian noise in high-reflectivity optical coatings," *Nature Photonics*, **7**, 644-650, 2013.

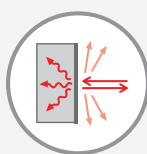


xtal mir™

Ultralow-loss single-crystal coatings **10× lower mid-infrared absorption**



Center wavelength
2 – 5+ μm



Optical losses
< 10 ppm (scatter + absorption)



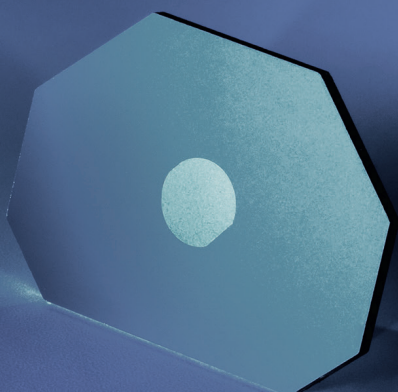
Bandwidth
200 – 400 nm FWHM

Other specifications

Optical transmission	Tunable, per customer request
Coating material	Single-crystal GaAs/AlGaAs
Substrate material	Typically silicon, other materials possible
Substrate diameter	0.5 – 1 inch (12.7 – 25.4 mm), other sizes available
Radius of curvature	> 10 cm
Surface quality	< 5 Å RMS micro-roughness
Durability	Similar to fused silica, cleaning instructions provided on request

Select scientific publications

B. J. Bjork, et. al. "Direct frequency comb measurement of OD + CO \rightarrow DOCO kinetics," Science, **354**, 444–448, 2016.
G. D. Cole, et. al. "High-performance near- and mid-infrared crystalline coatings," Optica, **3**, 647–656, 2016.

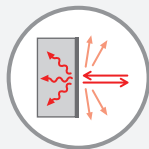


Thermally optimized optics **30× lower thermal resistivity**

Semiconductor films bonded to high thermal conductivity substrates



Center wavelength
900-5000 nm



Optical losses
< 5 ppm (scatter + absorption)



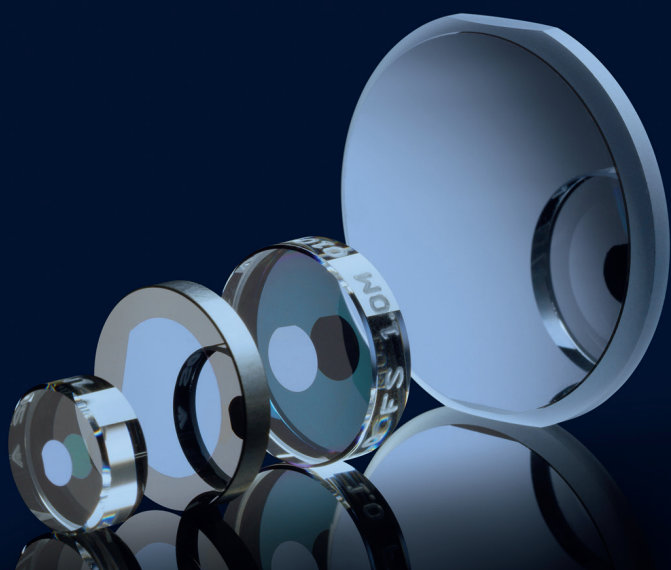
Coating thermal conductivity
> 30 Wm⁻¹K⁻¹

Other specifications

Optical transmission	Tunable, per customer request
Coating area	Substrate dependent, mm-to-cm size scale possible
Coating material	Single-crystal GaAs/AlGaAs
Substrate material	SiC, diamond, or other materials possible
Surface flatness	< 0.10 wave P-V measured @ 633 nm
Radius of curvature	> 0.1 m
Surface quality	< 5 Å RMS micro-roughness
Durability	Similar to fused silica, cleaning instructions provided on request

Select scientific publications

Z. Yang, et. al. "16 W DBR-free membrane semiconductor disk laser with dual-SiC-heatspreader," Electron. Lett., **54**, 430-432, 2018.
A. Diebold, et. al. "Optimized SESAMs for kilowatt-level ultrafast lasers," Opt. Express, **24**, 10512-10526, 2016.



 xtal custom™

Fully customizable solutions for direct-bonded components

Using our proprietary direct bonding technology, CMS offers custom services for the heterogeneous integration of any number of disparate material systems. With this interlayer- and stress-free process, we can fuse a wide variety of materials in the form of bulk components, wafers, or chips.



Example materials

Fused silica, Si, GaAs, Sapphire, SiC, Diamond, YAG, YVO4, Ti:Sapphire, etc.



Surface quality requirements

Micro-roughness < 1 nm;
bow/warp < 10 μ m;
P-V height variation < 100 nm



Size

< 5 mm \longrightarrow 200 mm



Thickness

> 1 μ m \longrightarrow 30 mm

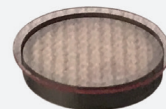
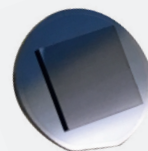


Radius of Curvature

Thickness dependent, \geq 1 cm

Select Examples

- Semiconductor active regions on SiC and diamond for thermally-optimized saturable absorbers and high-power emitters
- Electrically-conductive interface layers between single-crystal semiconductors
- Laser disks directly bonded to polished heat sink materials
- Buried dielectric layers between single-crystal materials and thin films
- Integration of non-lattice-matched semiconductor heterostructures
- Semiconductor films on "soft" materials
- Joining dielectric and semiconductor layers for silicon and integrated photonics
- Simplify manufacturing by eliminating film stress



Please contact us to discuss a solution
to your specific requirements.